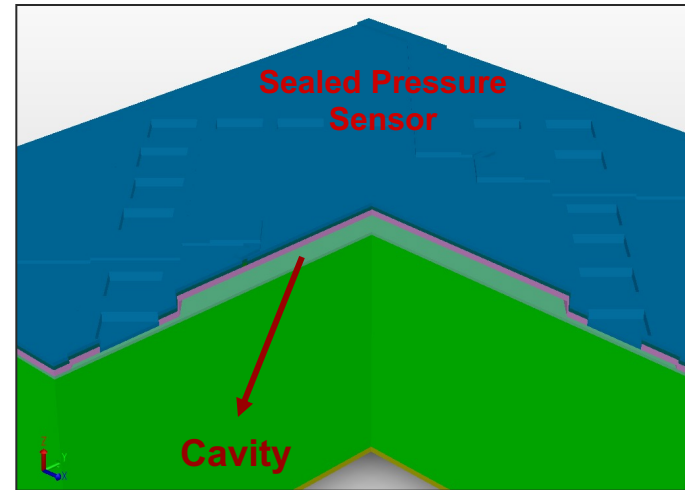
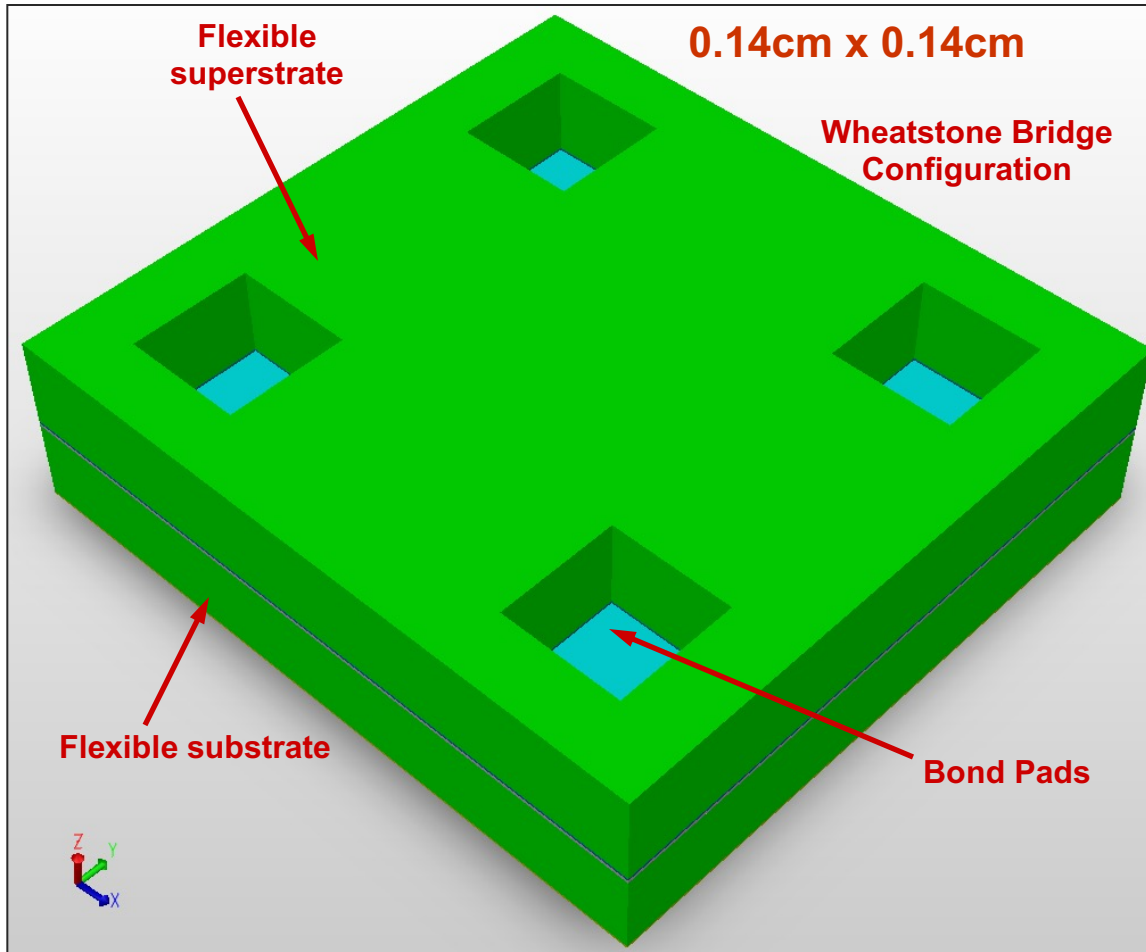

Absolute Pressure Sensors

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and M. Chitteboyina

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University of Texas at Arlington*

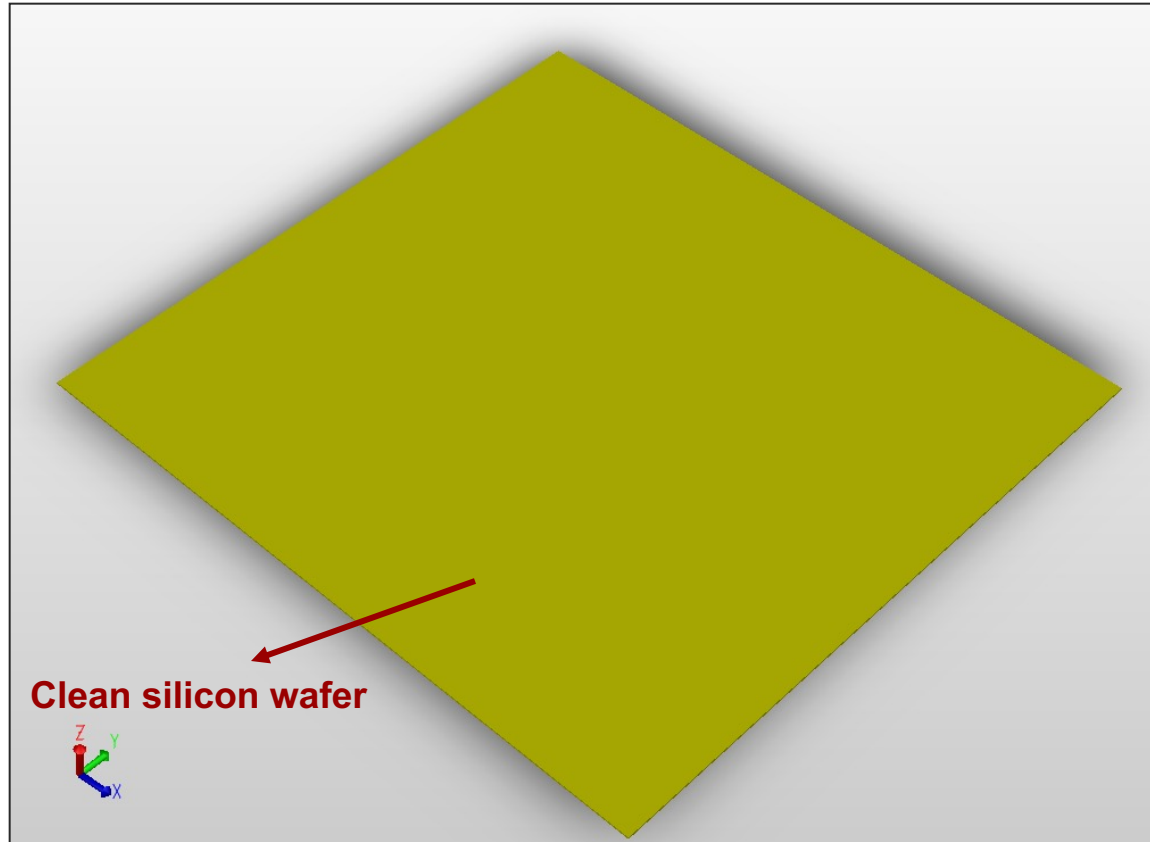
<http://www.uta.edu/engineering/nano/>

Absolute Pressure Sensor Model in CoventorWare

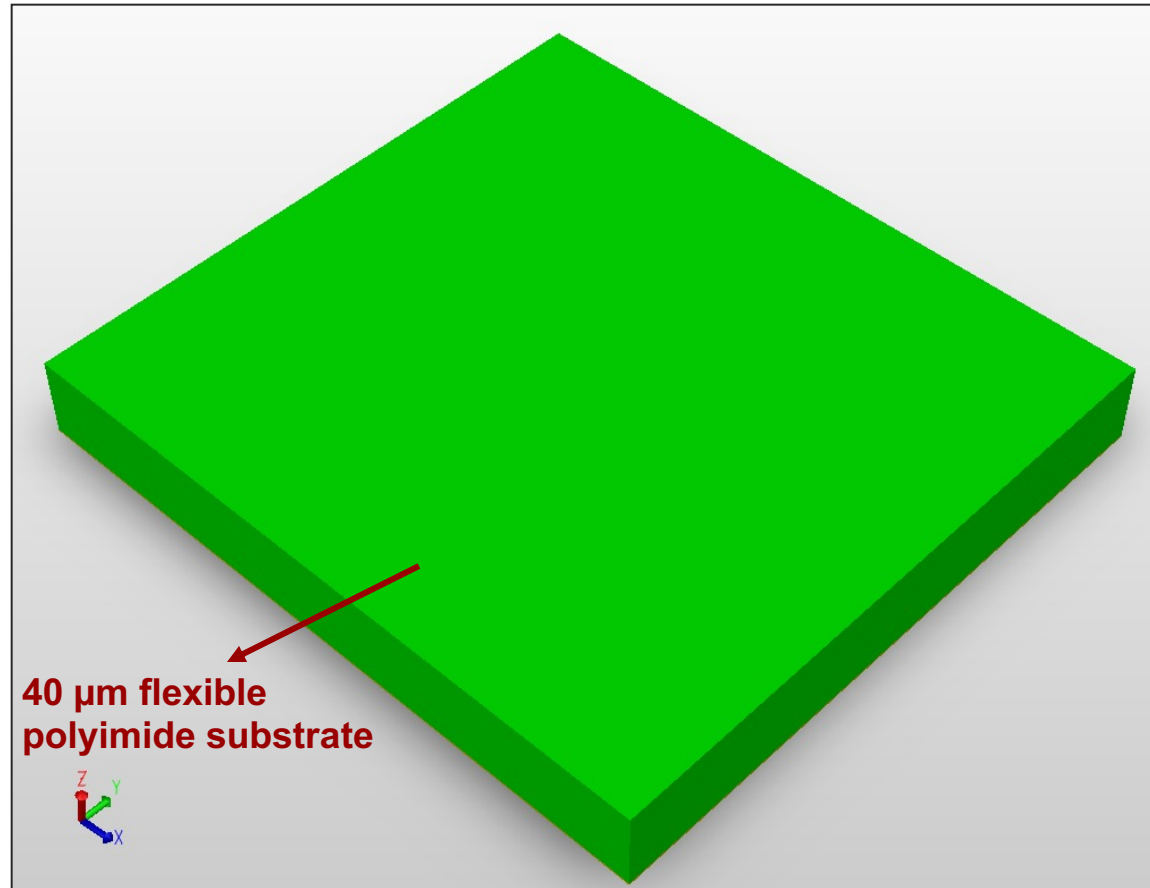


Stress, Strain and Displacement simulations for the pressure sensor is currently on-going

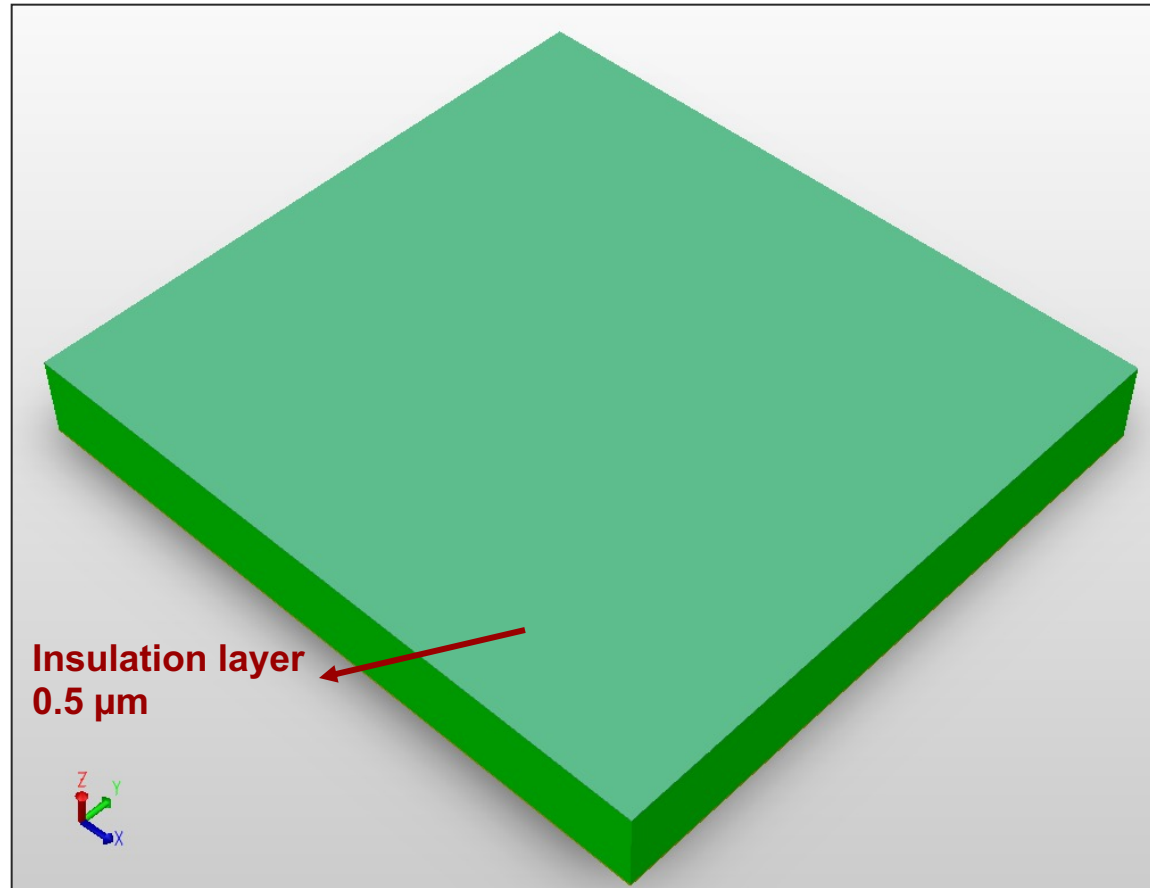
Fabrication Process Flow for the Absolute Pressure Sensor



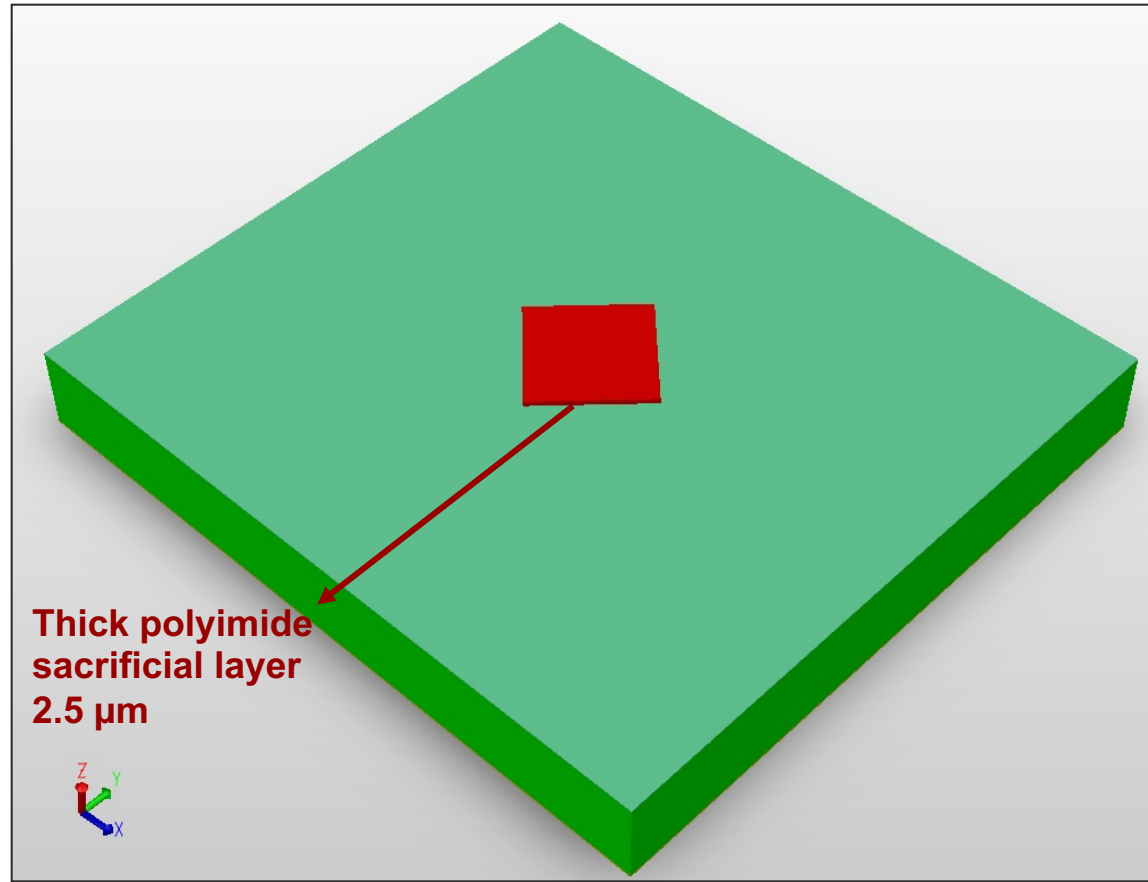
Fabrication Process Flow for the Absolute Pressure Sensor



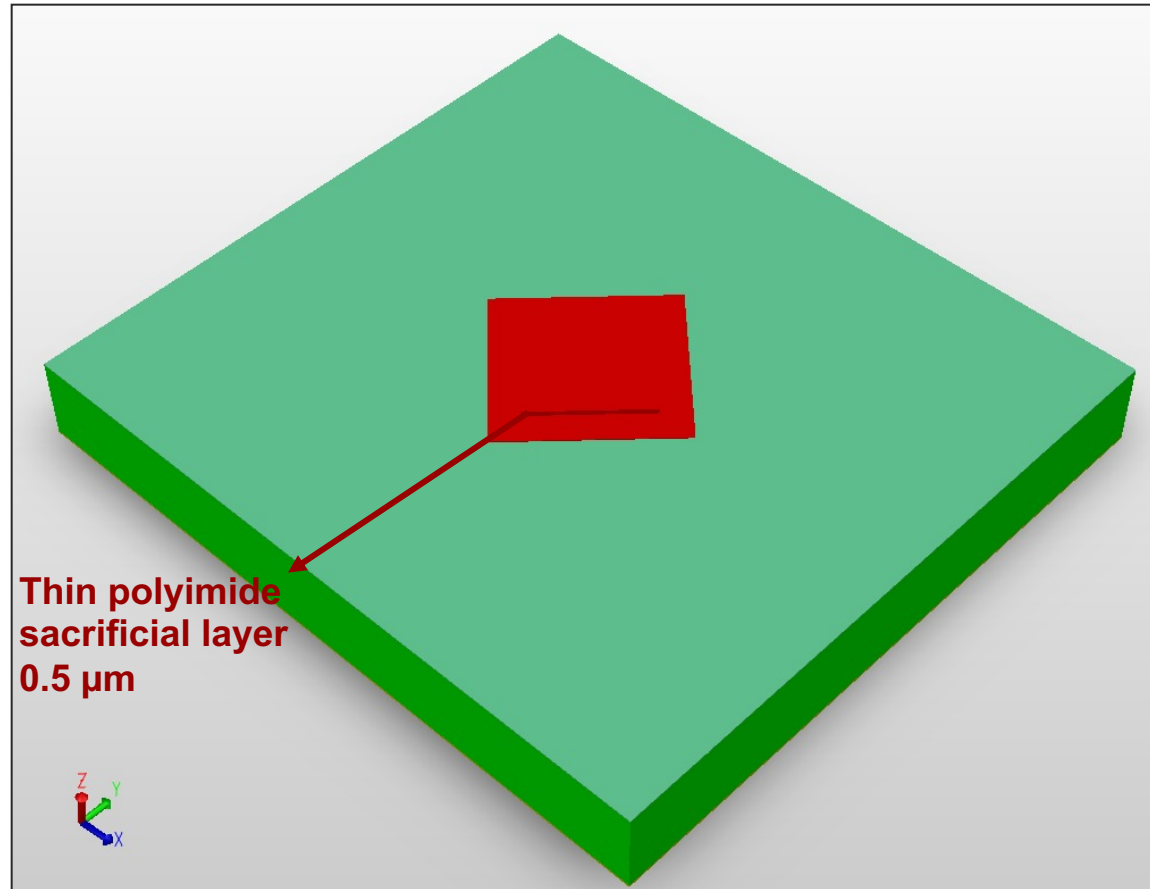
Fabrication Process Flow for the Absolute Pressure Sensor



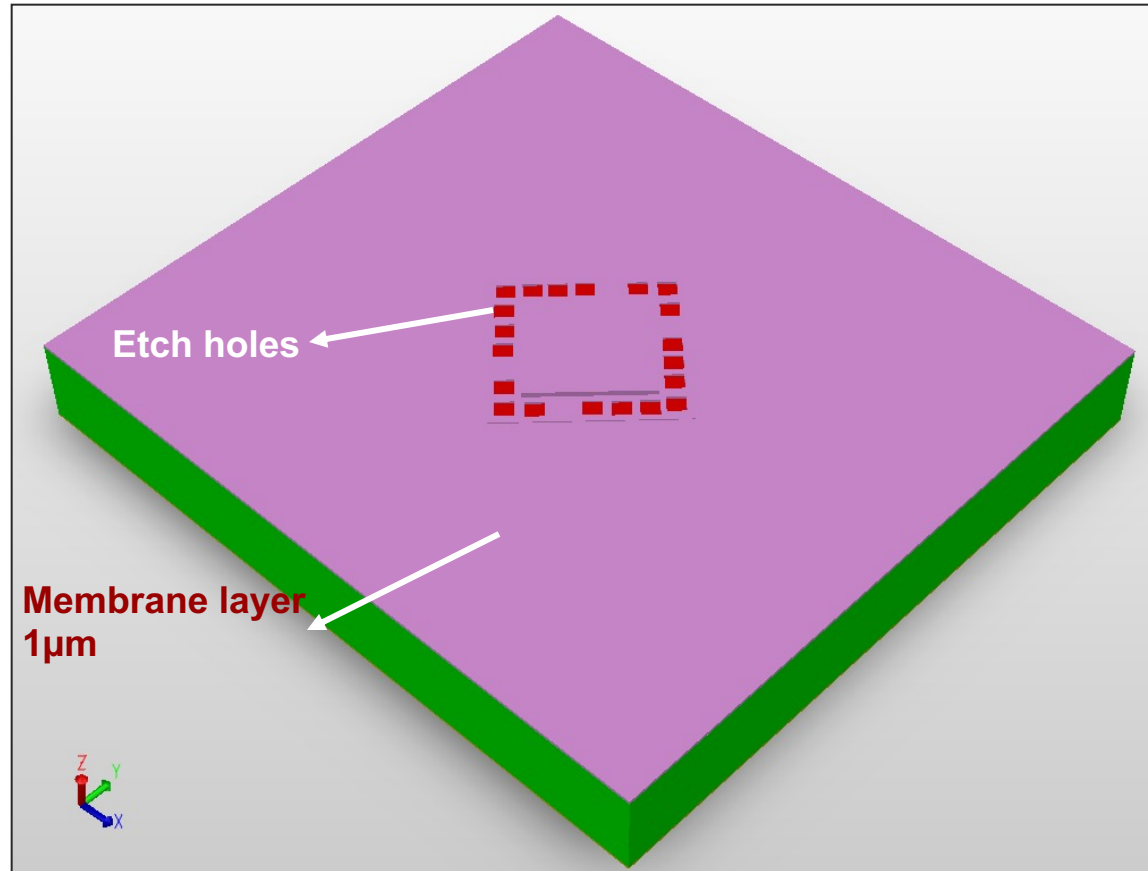
Fabrication Process Flow for the Absolute Pressure Sensor



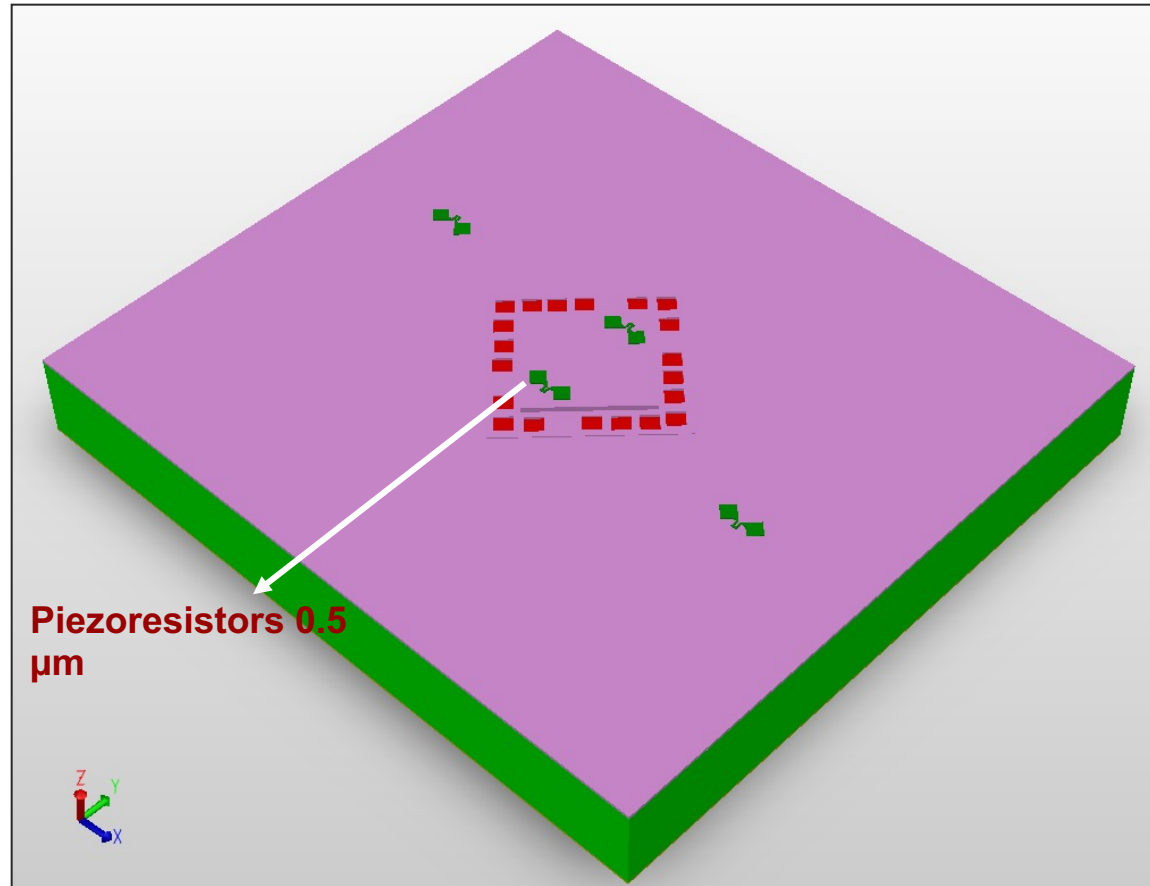
Fabrication Process Flow for the Absolute Pressure Sensor



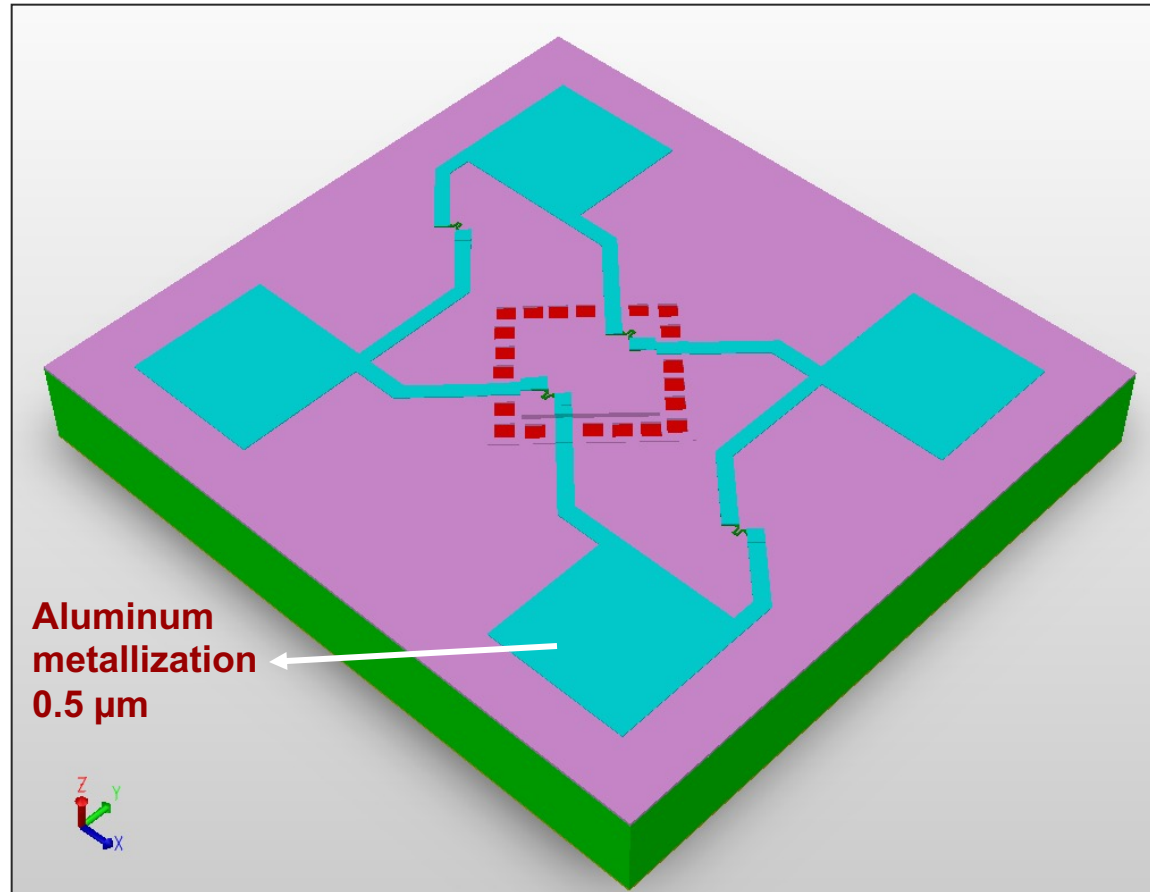
Fabrication Process Flow for the Absolute Pressure Sensor



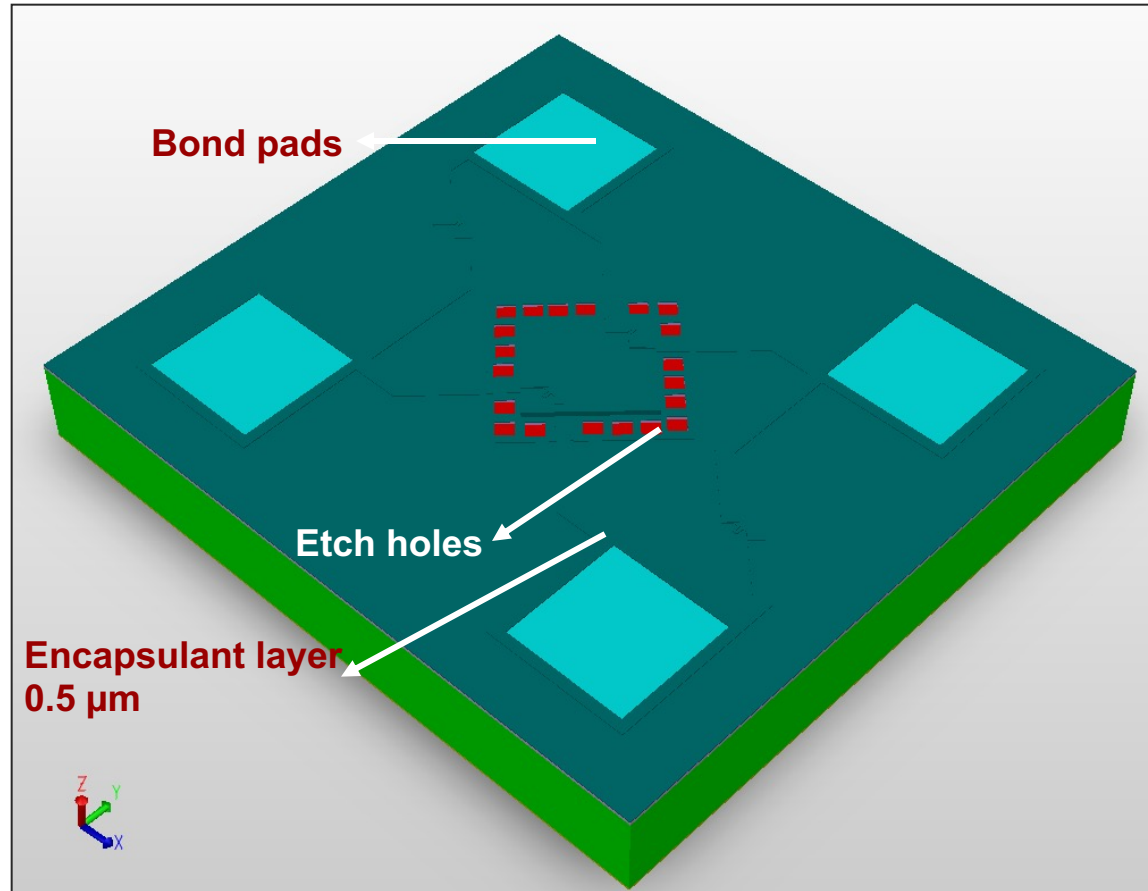
Fabrication Process Flow for the Absolute Pressure Sensor



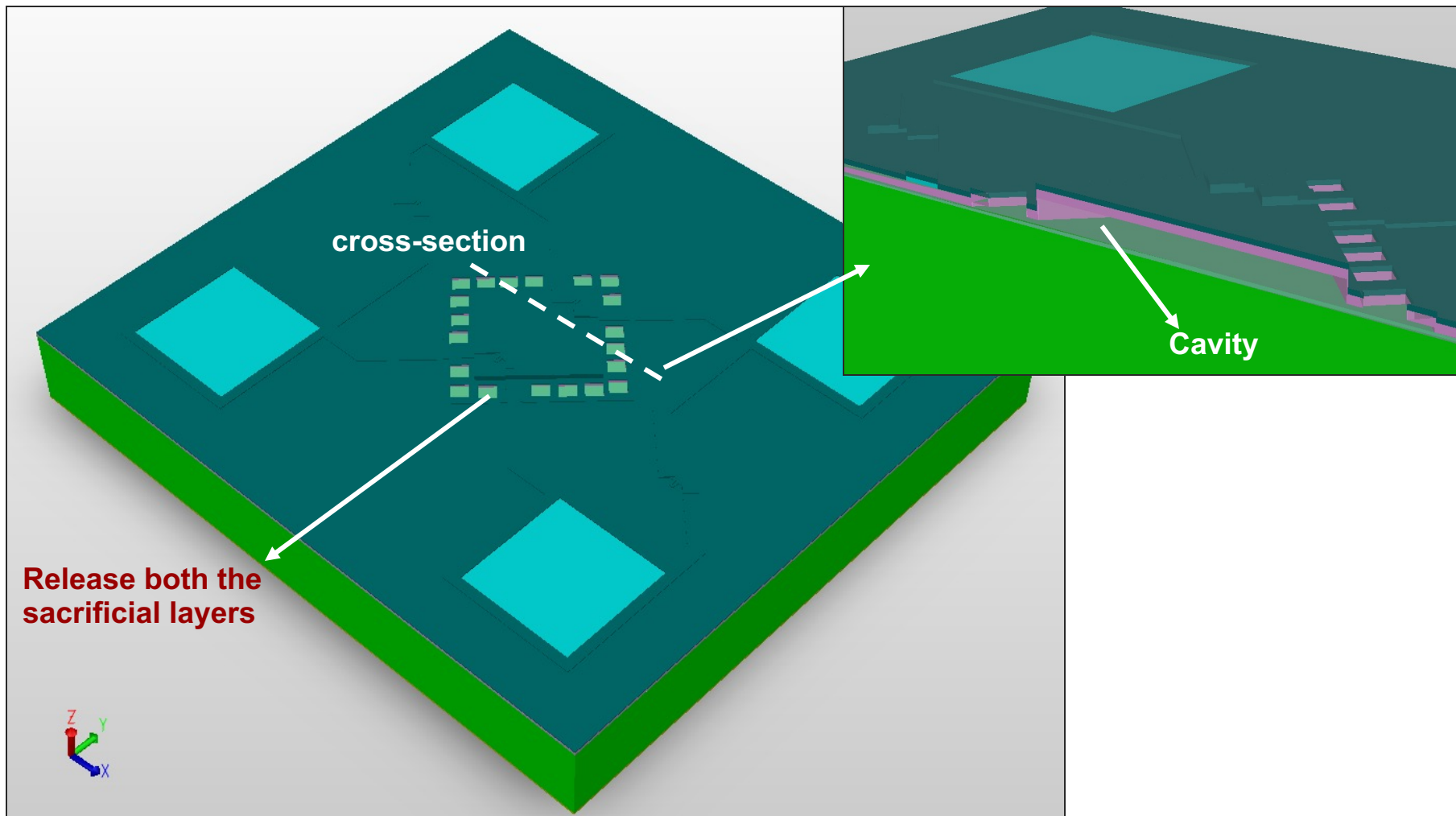
Fabrication Process Flow for the Absolute Pressure Sensor



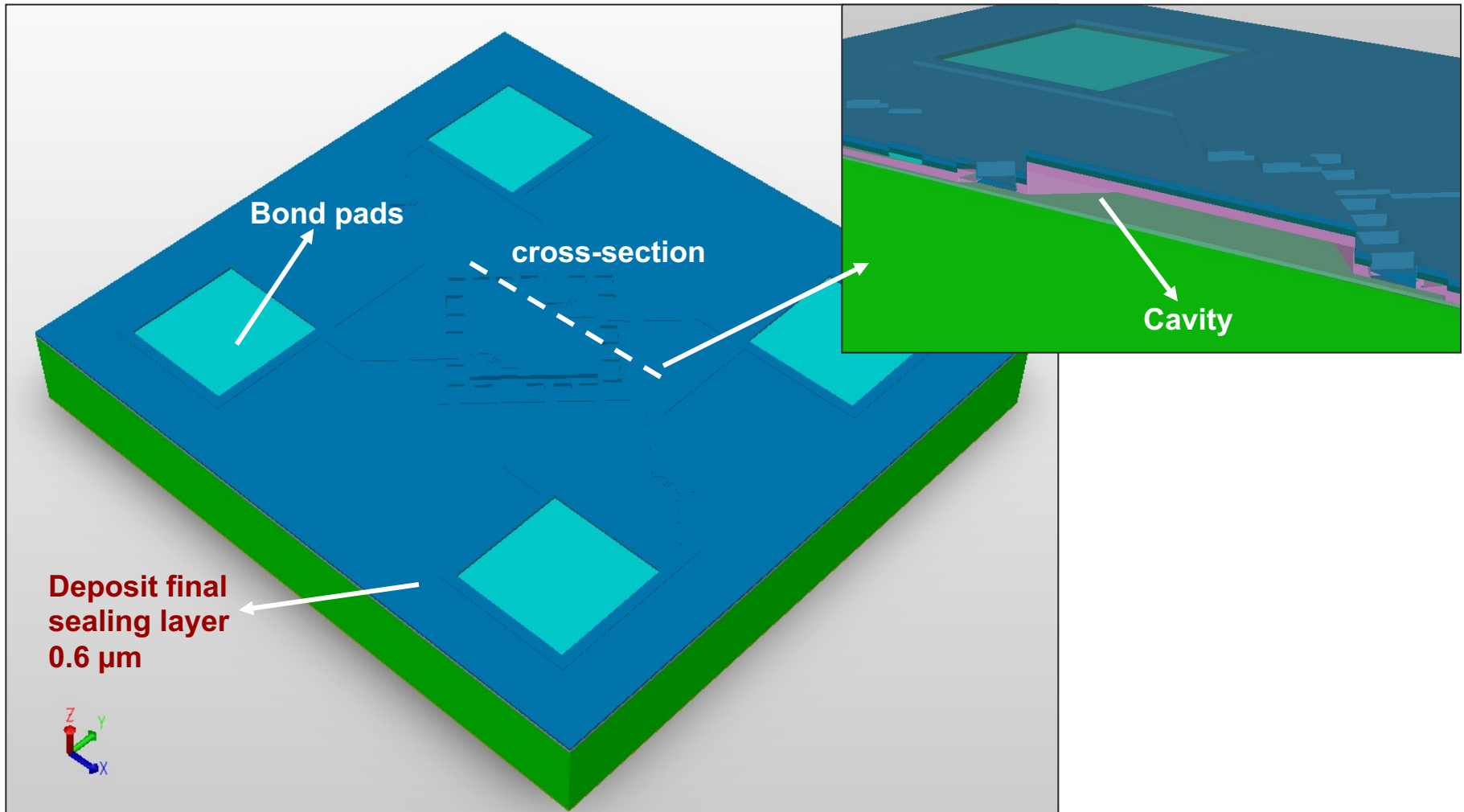
Fabrication Process Flow for the Absolute Pressure Sensor



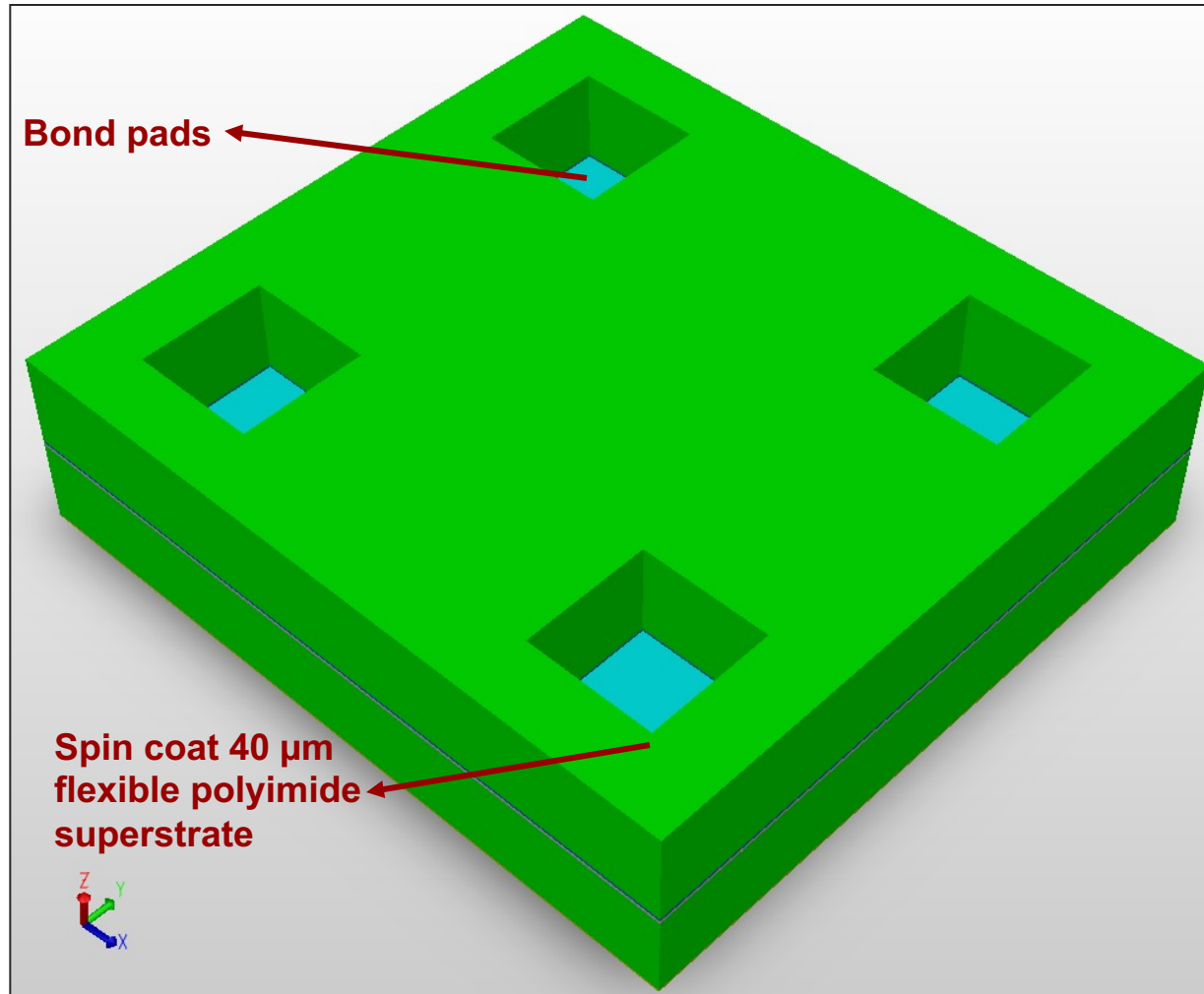
Fabrication Process Flow for the Absolute Pressure Sensor



Fabrication Process Flow for the Absolute Pressure Sensor



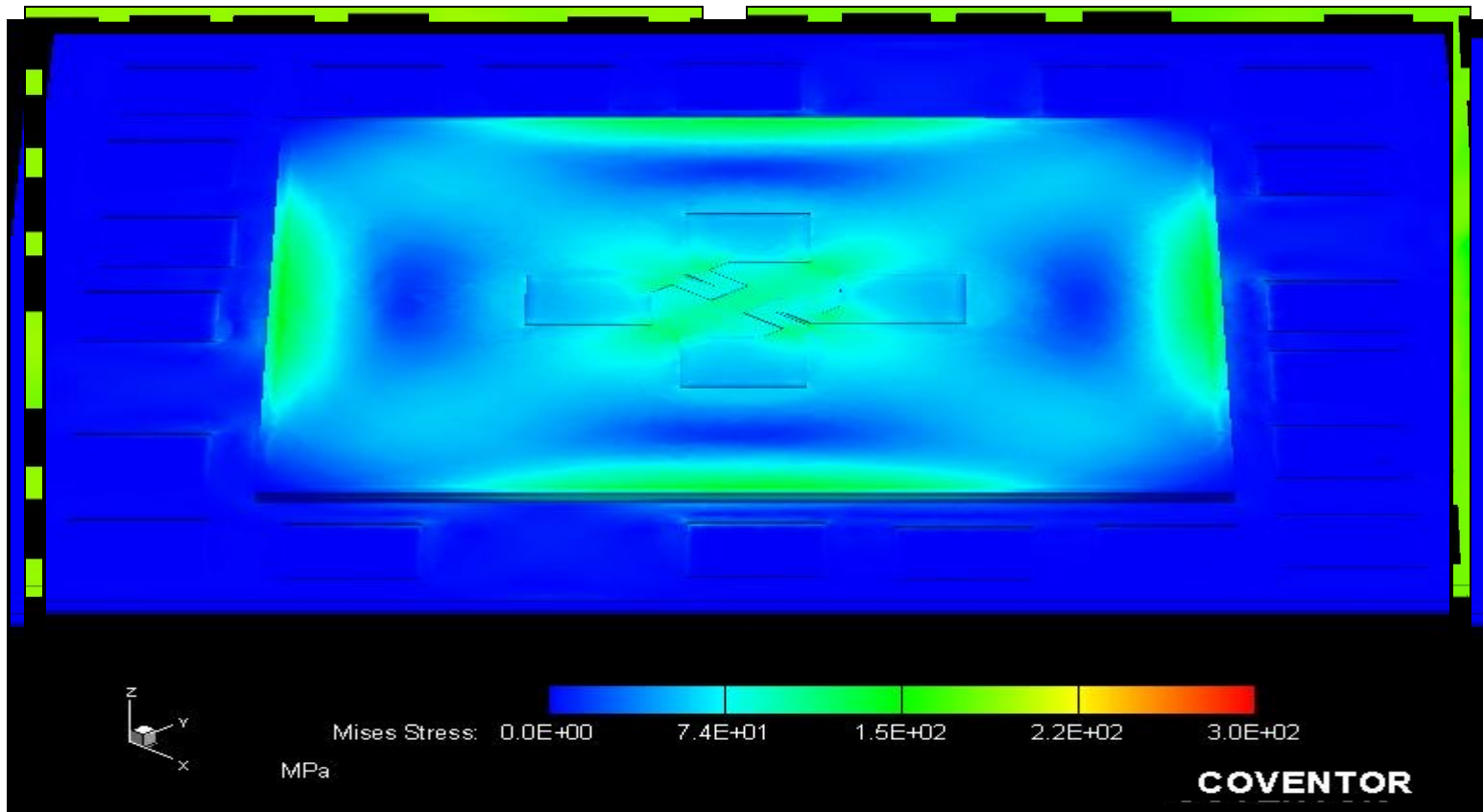
Fabrication Process Flow for the Absolute Pressure Sensor



Absolute Pressure Sensor Results

Sensor A (0.0 – 2.0 psi)

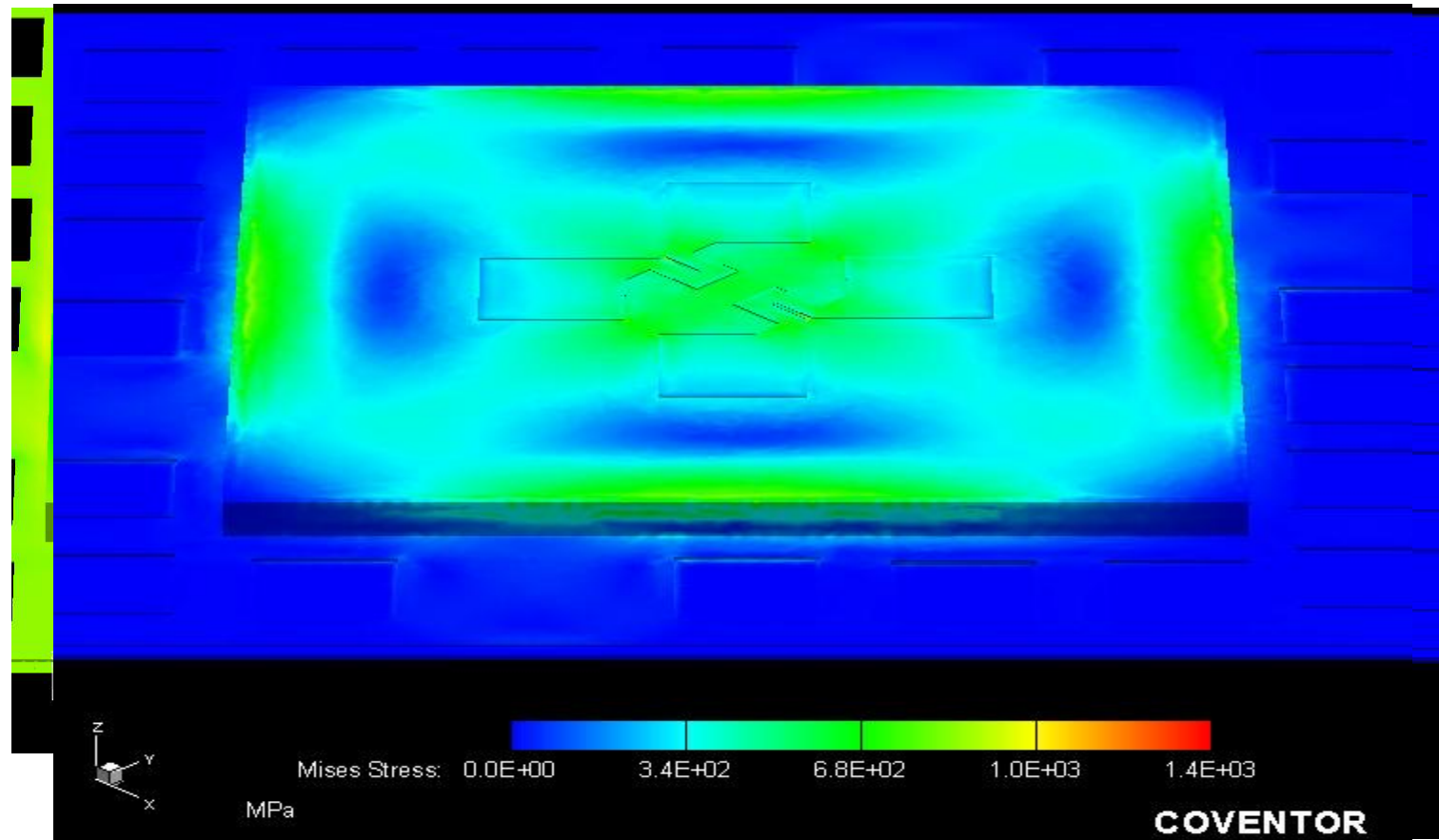
DISPLACEMENT PLOT
STRAIN YY PLOT MISES STRESS PLOT STRAIN XX PLOT



Absolute Pressure Sensor Design

Sensor H (14.0 – 16.0 psi)

DISPLACEMENT PLOT
STRAIN YY PLOT MISES STRESS PLOT STRAIN XX PLOT



Absolute Pressure Sensor Fabrication Steps

STEP 1

- On a clean wafer spin-coat $\sim 40 \mu\text{m}$ flexible polyimide as the substrate layer followed by 600 nm passivation layer

STEP 2

- Spin coat thick polyimide and cure

STEP 3

- Spin coat thin polyimide and cure

STEP 4

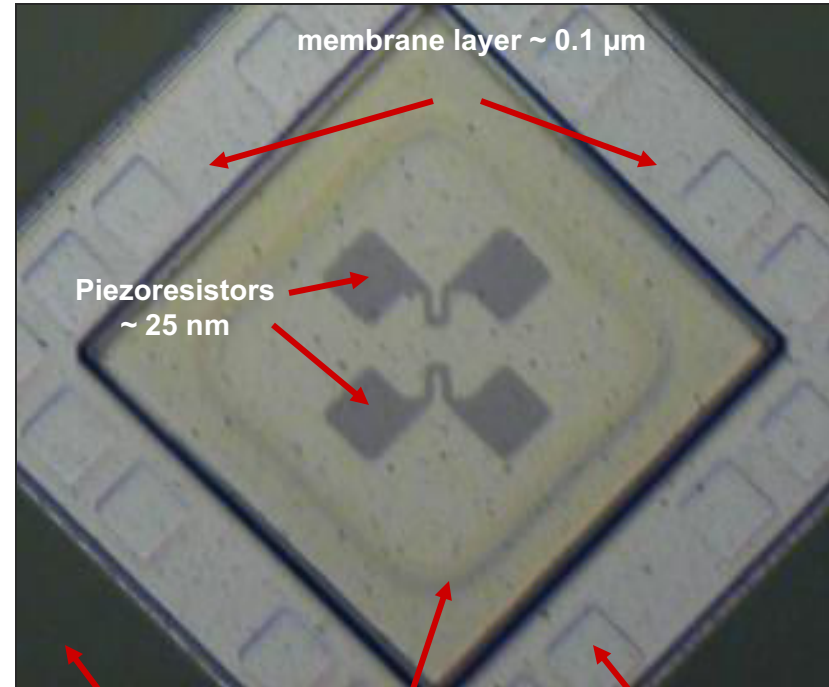
- Deposit $0.1 \mu\text{m}$ membrane layer

STEP 5

- Deposit $\sim 25 \text{ nm}$ piezoresistor layer

NEXT STEPS

- Deposit $\sim 500 \text{ nm}$ thick aluminum as the metallization layer
- Ash the sacrificial layer using oxygen plasma to suspend the membrane
- Deposit $0.5 \mu\text{m}$ encapsulation layer followed by $0.5 \mu\text{m}$ as the final sealing layer
- Etch the silicon wafer from the back side to get access to the bond pads and characterize the absolute pressure sensors

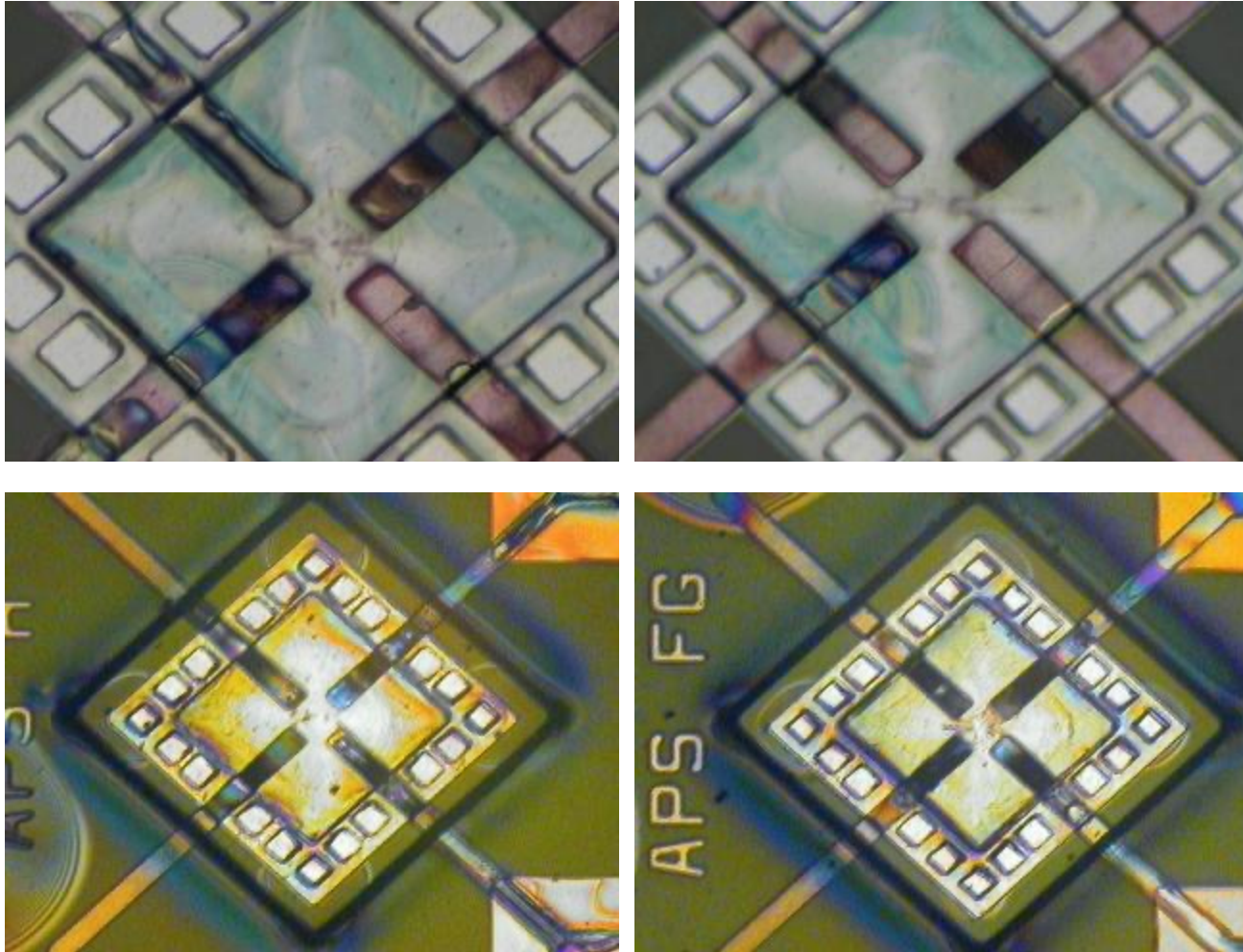


Passivation
layer $\sim 600 \text{ nm}$

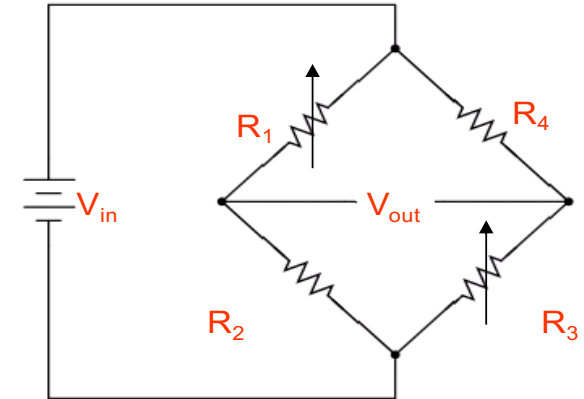
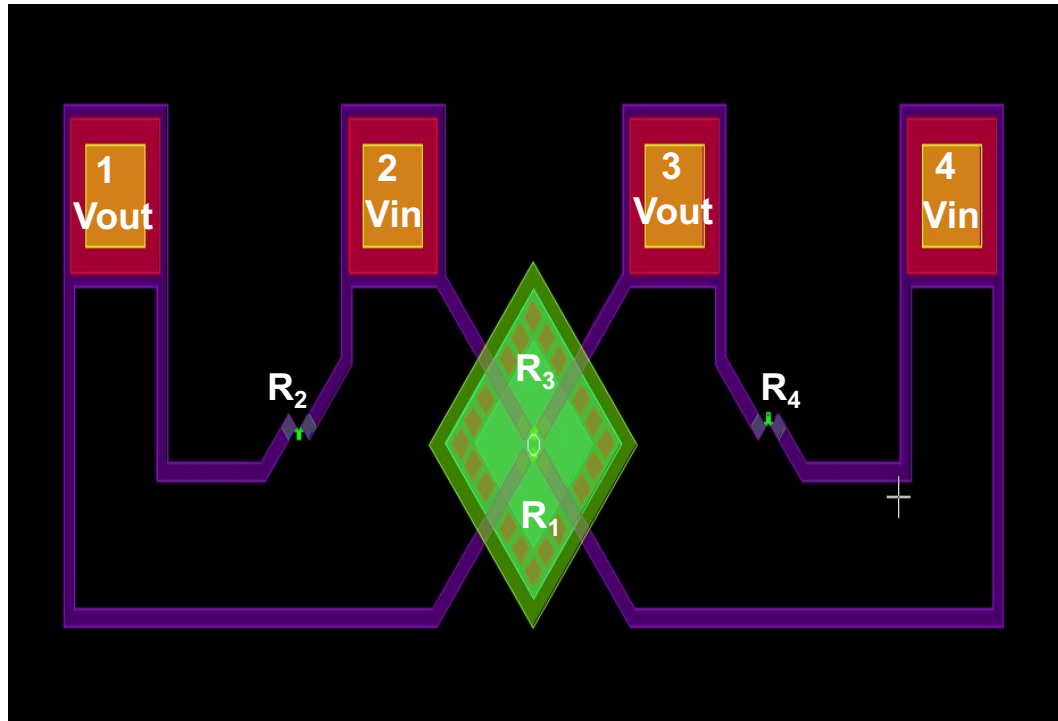
Thick Sacrificial
layer $\sim 7 \mu\text{m}$

Thin Sacrificial
layer $\sim 0.5 \mu\text{m}$

Absolute Pressure Sensor Fabrication Steps



Absolute Pressure Sensor Characterization



- ❑ The electrical circuit is complete with two active piezoresistors (R_1 and R_3) and two passive piezoresistors (R_2 and R_4) in a Wheatstone bridge configuration
- ❑ The current-voltage characteristics is plotted and the true resistances are found
- ❑ Pressure is applied on top of the membrane and the change in output voltage vs. input voltage is plotted